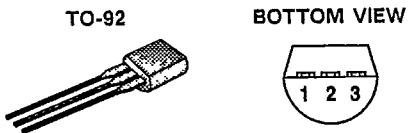


**ND2406 SERIES**

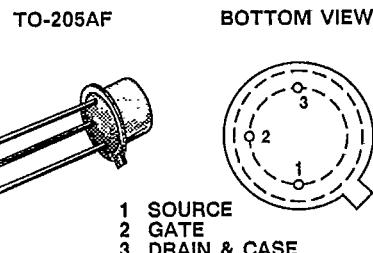
N-Channel Depletion-Mode MOS Transistors

 Siliconix  
incorporated

T-27-25



- 1 SOURCE
- 2 GATE
- 3 DRAIN



- 1 SOURCE
- 2 GATE
- 3 DRAIN & CASE

**PRODUCT SUMMARY**

PART NUMBER	V <sub>(BR)DSV</sub> (V)	r <sub>DSON</sub> (Ω)	I <sub>D</sub> (A)	PACKAGE
ND2406L	240	6	0.23	TO-92
ND2406B	240	6	0.57	TO-205AF

Performance Curves: VDDV24 (See Section 7)

**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)**

PARAMETERS/TEST CONDITIONS	SYMBOL	ND2406L	ND2406B <sup>2</sup>	UNITS
Drain-Source Voltage	V <sub>DS</sub>	240	240	V
Gate-Source Voltage	V <sub>GS</sub>	±30	±20	
Continuous Drain Current	I <sub>D</sub>	0.23	0.57	A
		0.14	0.36	
Pulsed Drain Current <sup>1</sup>	I <sub>DM</sub>	0.90	1	
Power Dissipation	P <sub>D</sub>	0.80	5	W
		0.32	2	
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C
Lead Temperature (1/16" from case for 10 seconds)	T <sub>L</sub>	300		

**THERMAL RESISTANCE**

THERMAL RESISTANCE	SYMBOL	ND2406L	ND2406B	UNITS
Junction-to-Ambient	R <sub>thJA</sub>	156	125	°C/W

<sup>1</sup>Pulse width limited by maximum junction temperature<sup>2</sup>Reference case for all temperature testing

ELECTRICAL CHARACTERISTICS <sup>1</sup>			LIMITS					
PARAMETER	SYMBOL	TEST CONDITIONS	TYP <sup>2</sup>	ND2406L		ND2406B		UNIT
				MIN	MAX	MIN	MAX	
<b>STATIC</b>								
Drain-Source Breakdown Voltage	V <sub>(BR)DSV</sub>	V <sub>GS</sub> = -9 V, I <sub>D</sub> = 10 μA	260	240		240		V
Gate-Source Cutoff Voltage	V <sub>GS(OFF)</sub>	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 10 μA	-2.8	-1.5	-4.5	-1.5	-4.5	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V V <sub>GS</sub> = ±20 V	±1		±10		±10	nA
Drain Cutoff Current	I <sub>D(OFF)</sub>	V <sub>DS</sub> = 180 V V <sub>GS</sub> = -9 V	0.04		1		1	μA
Drain Saturation Current <sup>3</sup>	I <sub>DS</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V	640	40		40		mA
Drain-Source On-Resistance <sup>3</sup>	r <sub>DS(ON)</sub>	V <sub>GS</sub> = 2 V, I <sub>D</sub> = 30 mA	3					Ω
		V <sub>GS</sub> = 0 V I <sub>D</sub> = 30 mA	3.5		6		6	
Forward Transconductance <sup>3</sup>	g <sub>FS</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 30 mA	7		15		15	
Common Source Output Conductance <sup>3</sup>	g <sub>os</sub>		110					mS
			70					μS
<b>DYNAMIC</b>								
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V V <sub>GS</sub> = -5 V f = 1 MHz	70		120		120	pF
Output Capacitance	C <sub>oss</sub>		20		30		30	
Reverse Transfer Capacitance	C <sub>rss</sub>		10		15		15	
<b>SWITCHING</b>								
Turn-On Time	t <sub>d(ON)</sub>	V <sub>DD</sub> = 25 V, R <sub>L</sub> = 830 Ω I <sub>D</sub> = 30 mA, V <sub>GEN</sub> = -5 V R <sub>G</sub> = 25 Ω (Switching time is essentially independent of operating temperature)	15					ns
	t <sub>r</sub>		75					
Turn-Off Time	t <sub>d(OFF)</sub>		40					
	t <sub>f</sub>		100					

NOTES: 1. T<sub>A</sub> = 25 °C unless otherwise noted, T<sub>C</sub> = 25 °C for ND2406B.  
 2. For design aid only, not subject to production testing.  
 3. Pulse test; PW = 300 μs, duty cycle ≤ 2%.